

# 1.6mm Silicon PD Chip datasheet

P/N : WS93-01C

## Feature

Si PIN photodiode chip

## Structure

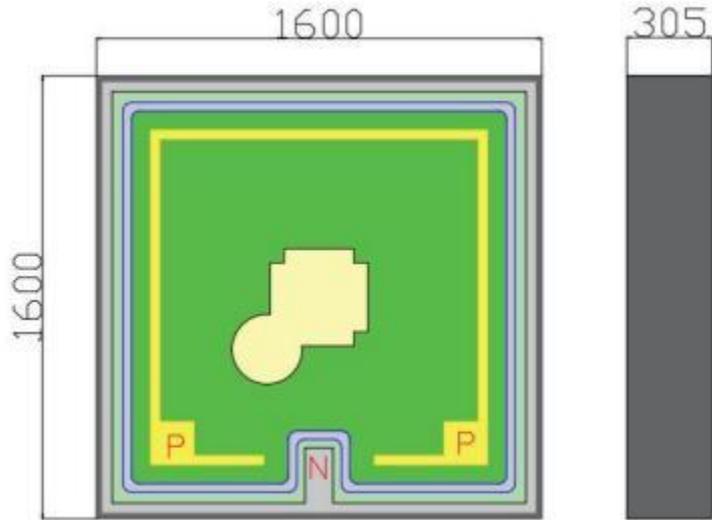
Planar type : PIN diode

Electrodes :

Top side ( Cathode ) : Aluminum

(Anode ) : Aluminum

Back side with SiO<sub>2</sub> covered



## DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	1346±10 x 1346±10			μm
Chip width	1600			μm
Chip length	1600			μm
Chip height	290	305	320	μm
Pad Area	153			μm

## Electro-Optical Characteristics ( @ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =10mA, H=0	0.5		1.2	V
Reverse Voltage	V <sub>br</sub>	I <sub>r</sub> =100μA, H=0	60			V
Reverse Dark Current	I <sub>d</sub>	V <sub>r</sub> =10V			10	nA
Sensitive Wavelength Range	λ		430		1100	nm
Reverse light Current	I <sub>L</sub>	V <sub>R</sub> =5V, 1 mW/cm <sup>2</sup> @940nm		10		uA
Capacitance	C <sub>j</sub>	V <sub>R</sub> =3V, f=1MHz		10		pF